

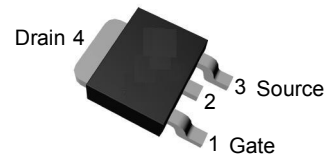
Features

- -100V/-10A,
 $R_{DS(ON)} = 250m\Omega$ (typ.) @ $V_{GS} = -10V$
 $R_{DS(ON)} = 260m\Omega$ (typ.) @ $V_{GS} = -4.5V$
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)
- 100% UIS + R_g Tested

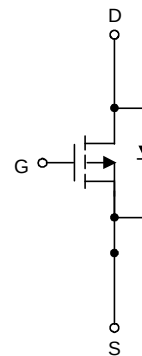
Applications

- Power Management in Desktop Computer or DC/DC Converters.

Pin Description



Top View of TO-252-2



P-Channel MOSFET

Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (T _A =25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		-100	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	°C
I _S	Diode Continuous Forward Current		-1	A
I _{DP}	300µs Pulse Drain Current Tested	T _C =25°C	-52	A
		T _C =100°C	-32	
I _D	Continuous Drain Current	T _C =25°C	-10	A
		T _C =100°C	-6	
P _D	Maximum Power Dissipation	T _C =25°C	50	W
		T _C =100°C	20	
R _{θJC}	Thermal Resistance-Junction to Case		2.5	°C/W
R _{θJA}	Thermal Resistance-Junction to Ambient		50	°C/W

Note : * Current limited by bond wire.

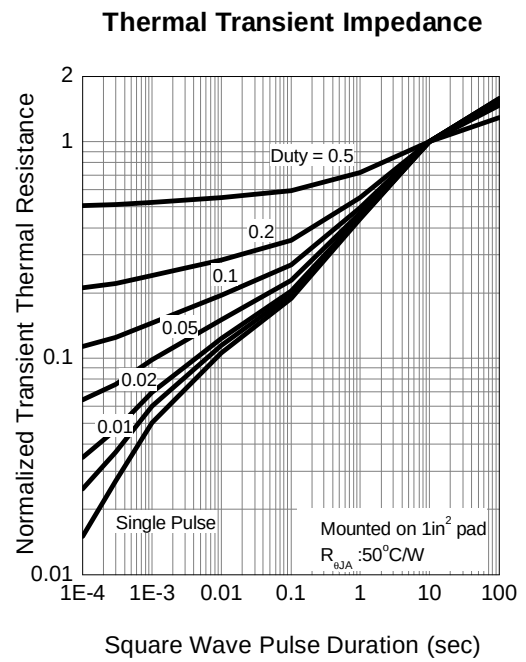
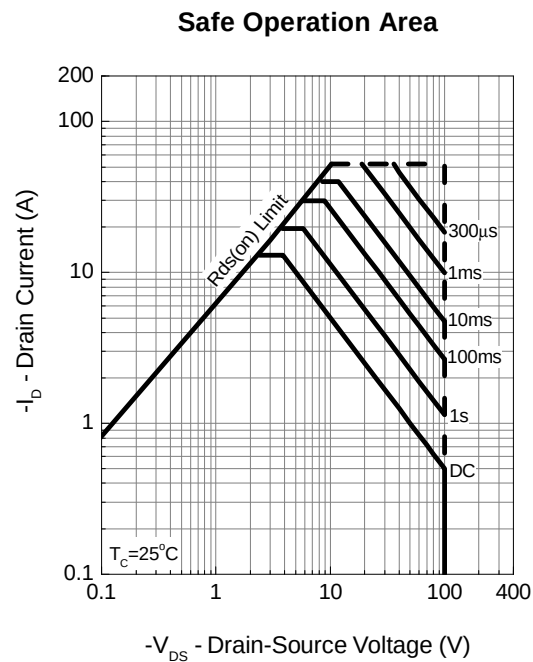
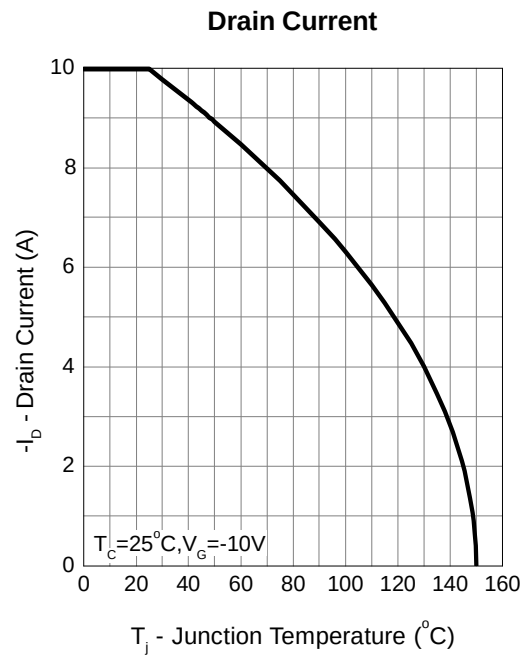
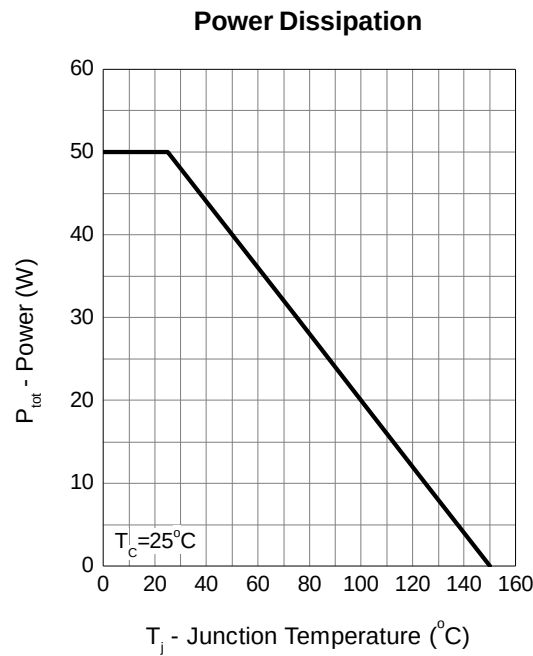
Electrical Characteristics (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	XPD100P250			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =-250μA	-100	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-80V, V _{GS} =0V	-	-	-1	μA
		T _J =85°C	-	-	-30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =-250μA	-1	-	-3	V
I _{GSS}	Gate Leakage Current	V _{GS} =±16V, V _{DS} =0V	-	-	±10	μA
R _{DS(ON)} ^a	Drain-Source On-state Resistance	V _{GS} =-10V, I _{DS} =-5A	-	250	300	mΩ
		V _{GS} =-4.5V, I _{DS} =-3A	-	260	340	
Diode Characteristics						
V _{SD} ^a	Diode Forward Voltage	I _{SD} =-1A, V _{GS} =0V	-	-0.75	-1.1	V
t _{rr}	Reverse Recovery Time	I _{DS} =-7.8A,	-	34	-	ns
Q _{rr}	Reverse Recovery Charge	di _{SD} /dt=100A/μs	-	59	-	nC
Dynamic Characteristics ^b						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-30V, Frequency=1.0MHz	-	1050	-	pF
C _{oss}	Output Capacitance		-	70	-	
C _{rss}	Reverse Transfer Capacitance		-	40	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =-30V, R _L =30Ω, I _{DS} =-1A, V _{GEN} =-10V, R _G =6Ω	-	11	21	ns
t _r	Turn-on Rise Time		-	10	19	
t _{d(OFF)}	Turn-off Delay Time		-	55	100	
t _f	Turn-off Fall Time		-	30	55	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} =-50V, V _{GS} =-10V, I _{DS} =-7.8A	-	20.9	38	nC
Q _{gs}	Gate-Source Charge		-	4.2	-	
Q _{gd}	Gate-Drain Charge		-	5.2	-	

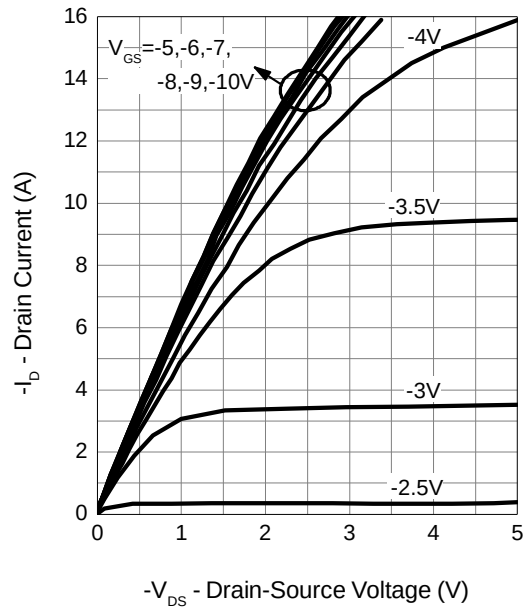
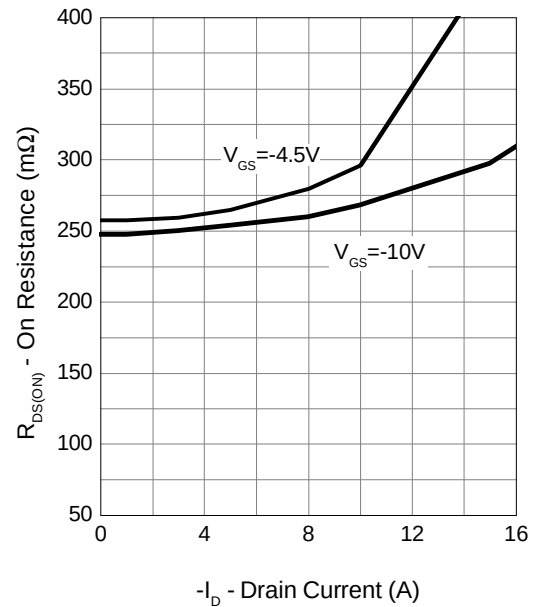
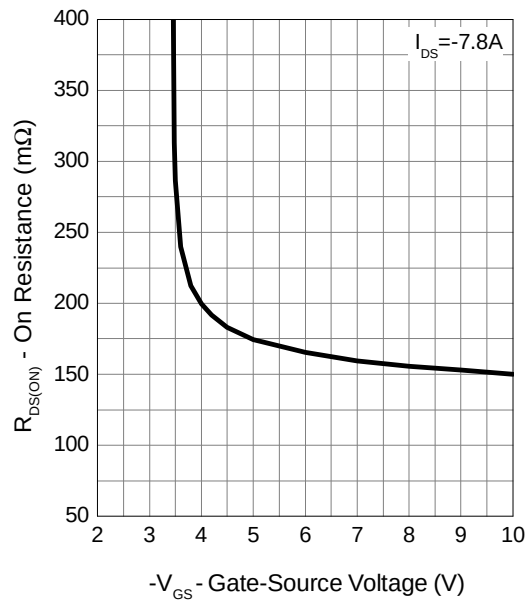
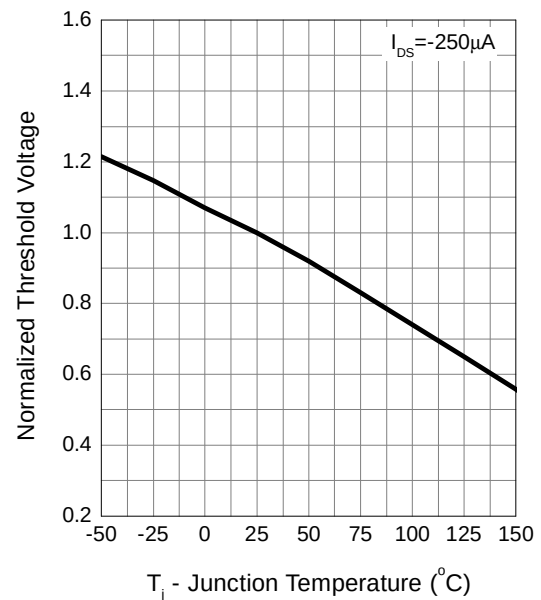
Note a : Pulse test ; pulse width≤300μs, duty cycle≤2%.

Note b : Guaranteed by design, not subject to production testing.

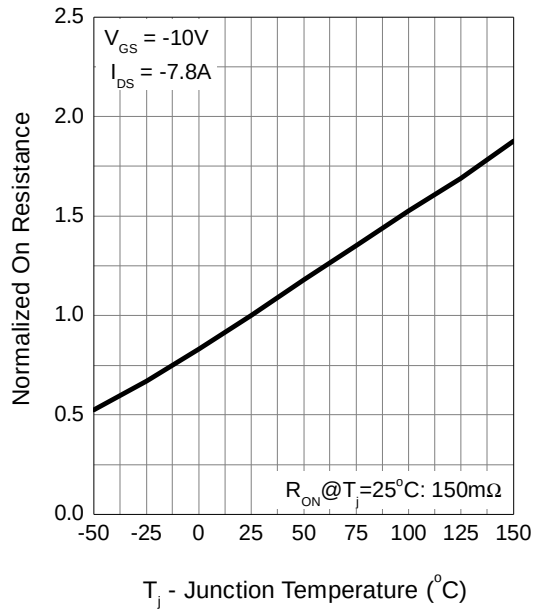
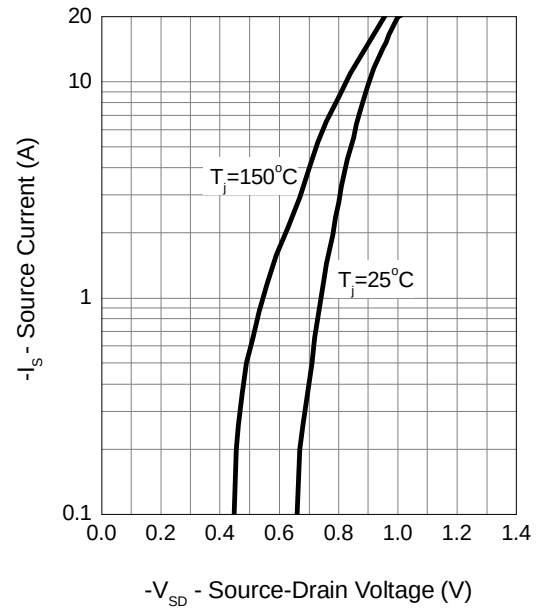
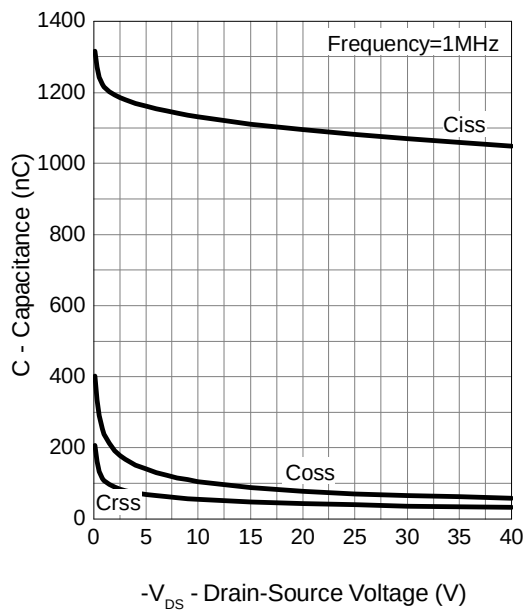
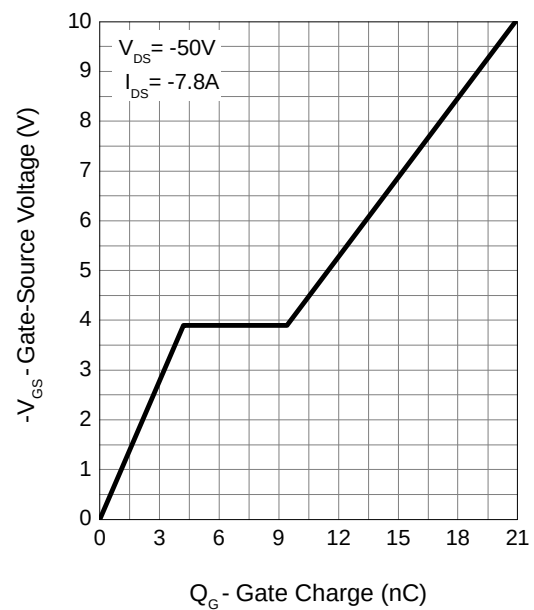
Typical Operating Characteristics



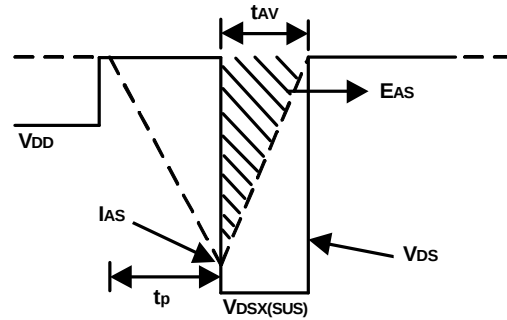
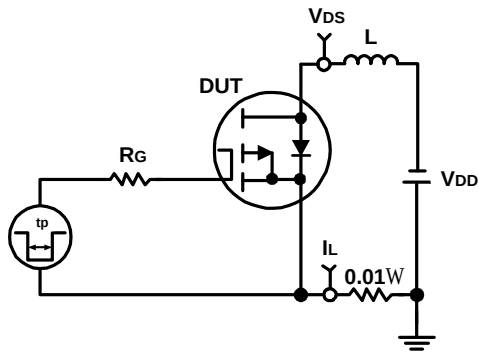
Typical Operating Characteristics (Cont.)

Output Characteristics

Drain-Source On Resistance

Gate-Source On Resistance

Gate Threshold Voltage


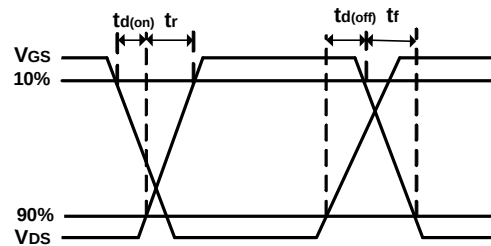
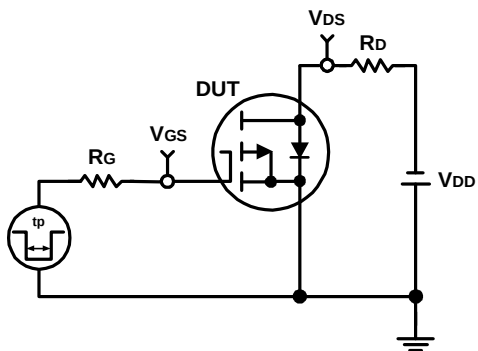
Typical Operating Characteristics (Cont.)

Drain-Source On Resistance

Source-Drain Diode Forward

Capacitance

Gate Charge


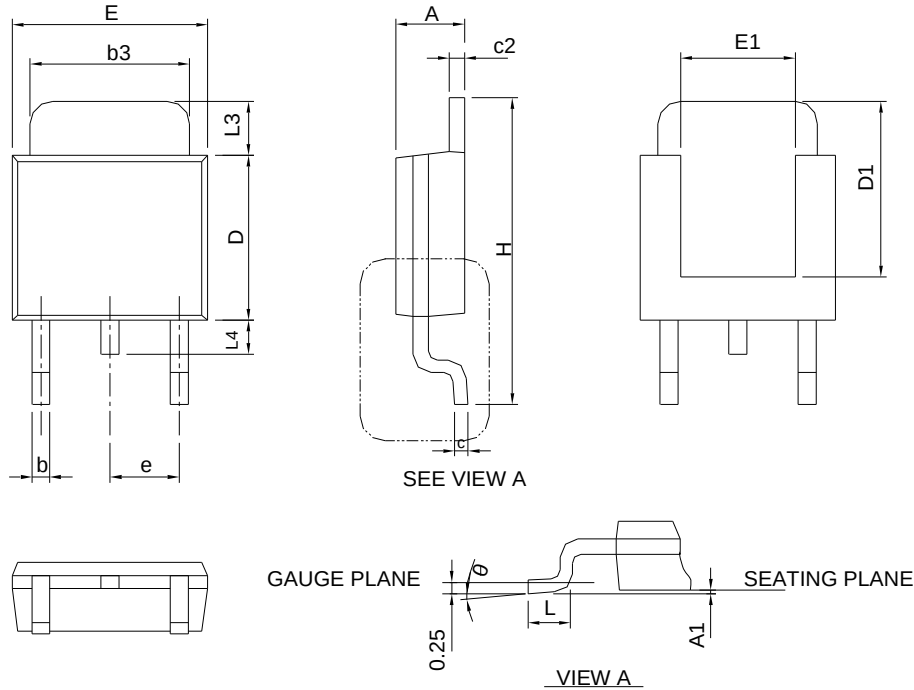
Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms



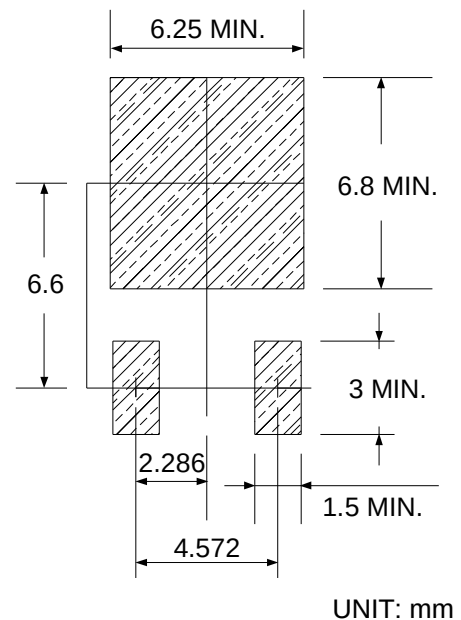
Package Information



SYMBOL	TO-252-2			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.39	0.086	0.094
A1	-	0.13	-	0.005
b	0.50	0.89	0.020	0.035
b3	4.95	5.46	0.195	0.215
c	0.46	0.61	0.018	0.024
c2	0.46	0.89	0.018	0.035
D	5.33	6.22	0.210	0.245
D1	4.57	6.00	0.180	0.236
E	6.35	6.73	0.250	0.265
E1	3.81	6.00	0.150	0.236
e	2.29 BSC		0.090 BSC	
H	9.40	10.41	0.370	0.410
L	0.90	1.78	0.035	0.070
L3	0.89	2.03	0.035	0.080
L4	-	1.02	-	0.040
θ	0°	8°	0°	8°

Note : Follow JEDEC TO-252 .

RECOMMENDED LAND PATTERN



UNIT: mm